Cypress Semiconductor
Product Qualification Report

G000002 VERSION 1.0
May, 2001

2Meg Synchronous SRAM WaferTech 0.35um	
GVT7164B36Y / GVT7164S36Y	**64 x 36**
GVT7164T18Y	**64T18**
GVT71128B18Y / GVT71128D18Y	**128 x 18**

CYPRESS TECHNICAL CONTACT FOR QUALIFICATION DATA:

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PRODUCT QUALIFICATION HISTORY

Qual Report	Description of Qualification Purpose	Date Comp
G990003	New Technology, WaferTech 0.35um / 4Meg, Synchronous SRAM, GVT71128E36Y and product family and bonding option	Jan 98
G000002	New Product, 2Meg, Synchronous SRAM. GVT7164B36Y, and product family and bonding option, WaferTech 0.35um	Oct 00

PRODUCT DESCRIPTION (for qualification)		
Qualification Purpose: 2Meg, Synchronous SRAM, GVT7164B36Y, and product family and bonding option, WaferTech.35um		
Marketing Part #:	GVT7164B36Y	
Device Description	3.3V, Commercial/Industrial available in 100-pin TQFP package	
Cypress Division:	Cypress Semiconductor Corporation – Synchronous Memory Product Division (MPD)	
Overall Die (or Mask) REV Level (pre-requisite for qualification):		Rev. Y
What ID markings on Die:	GVT7164B6	

Galvantech Part #	Product Information	TSMC Part #
GVT7164T18Y		TM5725
GVT7164B36Y		TM5725
GVT7164S36Y		TM5725
GVT71128B18Y	B and D are bonding option	TM5725
GVT71128D18Y	128B18 and 64T18 are bonding option	TM5725

TECHNOLOGY/FAB PROCESS DESCRIPTION			
Number of Metal Layers:	2	Metal Composition:	Metal 1: 4,000Å Ti/1,000Å TiN/4,000Å AlCu/250Å TiN Metal 2: 1,500Å Ti/6,000Å AlCu/250Å TiN
Passivation Type and Materials:	2K PE-Oxide + 6.5K PE-Nitride		
Free Phosphorus contents in top glass layer(%):	0		
Generic Process Technology/Design Rule (μ-drawn):	CMOS, Double Metal, 0.35um Technology		
Gate Oxide Material/Thickness (MOS):	70A SiO2		
Name/Location of Die Fab (prime) Facility:	WaferTech WA, USA		
Die Fab Line ID/Wafer Process ID:	WaferTech 0.35um		

PACKAGE AVAILABILITY

PACKAGE	ASSEMBLY SITE FACILITY
100-pin TQFP	**SPIL/** ASEK

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	A100
Package Outline, Type, or Name:	100-pin Thin Quad Flat Package (TQFP)
Mold Compound Name/Manufacturer:	Hitachi 7320
Mold Compound Flammability Rating:	V-O per UL94
Oxygen Rating Index:	＞28%
Lead Frame Material:	Copper
Lead Finish, Composition / Thickness:	Solder Plate, 85%Sn, 15%Pb
Die Backside Preparation Method/Metallization:	N/A
Die Separation Method:	Wafer Saw
Die Attach Supplier:	Sumitomo
Die Attach Material:	Sumitomo 7320
Bond Diagram Designation	GVT7164B364-0
Wire Bond Method:	Thermosonic
Wire Material/Size:	Au, 1.2um
Thermal Resistance Theta JA °C/W:	29.9 °C/W
Package Cross Section Yes/No:	N/A
Assembly Process Flow:	49-78002
Name/Location of Assembly (prime) facility:	SPIL

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	CHIPMOS
Fault Coverage:	100%

RELIABILITY TESTS PERFORMED PER SPECIFICATION REQUIREMENTS

Stress/Test	Test Condition (Temp/Bias)	Result P/F
High Temperature Operating Life Latent Failure Rate	Dynamic Operating Condition, Vcc = 3.6V, 150°C (500hrs)	R
High Accelerated Saturation Test (HAST	130C, 85%RH,	P
Temperature Cycle	MIL-STD-883C, Method 1010, Condition C, -65°C to 150°C	P
Pressure Cooker Test	100%RH, 15PSIG	P
High Temperature Storage (Plastic)	150C	P
Electrostatic Discharge Human Body Model (ESD-HBM)	MIL-STD-883C (2000V)	P
Thermal Shock	-65°C to 150°C	P
Latchup Sensitivity	In Accordance with JEDEC 17. 6.5V, >900mA	P

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal AF[3]	Failure Rate[4]
High Temperature Operating Life Early Failure Rate	512	0	N/A	N/A	0 PPM
High Temperature Operating Life[2,3] Long Term Failure Rate	1,920,312 DHRs	1	0.7	170	6 FIT

[1] Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.
[2] Chi-squared 60% estimations used to calculate the failure rate.
[3] Thermal Acceleration Factor is calculated from the Arrhenius equation

$$AF = \exp\left[\frac{E_A}{k}\left[\frac{1}{T_2} - \frac{1}{T_1}\right]\right]$$

where:

E_A =The Activation Energy of the defect mechanism.
k = Boltzmann's constant = 8.62×10^{-5} eV/Kelvin.
T_1 is the junction temperature of the device under stress and T_2 is the junction temperature of the device at use conditions.

[4] **EFR and LFR FIT Rate based on Technology and Product Qualification**

Product Qualification

Precondition - JESD-A113-B

WaferTech .25um 2meg			Condition: Level 3, 192 Hrs @ 30°C/60% RH			
Device	Lot Number	Package	In	Out	Rej	Yield
GVT7164B36Y	W10517AA	100TQFP	77	77	7	100.0%

HTOL - MIL-STD-883, Method 3015

WaferTech.25um Technology, 2Meg			Condition: Dynamic BI @ 150C, Vcc=3.6V, Vih =3V					Reliabilty
Device	Lot Number	Package	Read(hr	0	24	184	500	TDH
GVT7164B36Y	W10517AA	100TQFP	SS/Rej	77	77	77	77	35,000
					0	0	0	-

ESD - MIL-STD-883, Method 3015

WaferTech .25um 2meg			Condition: Human Body Model					
Device	Lot Number	Package	Stress	1kV	1.5kV	2kV	2.5kV	3kV
GVT7164B36Y	W10517AA	100TQFP	SS/Rej			3		
						0		

A blank entry indicates ESD stress was not performed for that level.

ESD Rating:

Device	Voltage
GVT7164B36Y	2kV

IC Latch-up - JESD78

WaferTech .25um 2meg			Stress Condtions				Vcc		Input/IO
Device	Lot Number	Package	Read	Condition	Results	Forcing	IN = HI	IN = LO	Neg (Hi/Lo)
GVT7164B36Y	W10517AA	100TQFP	SS/Rej	Class II	6	Voltage	5.4V	5.4V	-1.8V
				(125C)	0	Current	< 500mA	< 500mA	-100ma

HTOL Reliability Monitor					
Dynamic BI @ 150C, Vcc=3.63V					
Read hr	0	24	184	368	500
SS	1960	-	1960	1959	725
Rej	0	0	0	0	1
SS	1885	1885	1885	1885	1885
Rej	0	0	0	0	0

HTOL Qualification					
Read hr	0	24	184	368	500
SS	435	435	435	-	435
Rej	0	0	0	-	0

WAFER LEVEL

Electromigration (EM)

Pattern	Fail Criteria >20% Change	Jmax>Jtsmc @ 0.1% CUM failure, 100k hoursn @ 110C, sample size 30 units. (Units in mA/um)					
		C92050		C92051		C92054	
M1 (0.4um)	1.0mA/um	>1.9	Pass	>3.74	Pass	>3.71	Pass
M1 (7um)	1.0mA/um	2.36	Pass	>1.59	Pass	>1.48	Pass
M2 (0.45um)	1.2mA/um	>5.61	Pass	>5.56	Pass	>5.46	Pass
M2 (7um)	1.2mA/um	2.32	Pass	2.16	Pass	2.07	Pass
Via (0.4 x 0.4)	0.34mA/um	>0.94	Pass	>0.94	Pass	>0.93	Pass
Via (0.45 x .45)	0.3mA/um	>1.04	Pass	>1.06	Pass	>1.05	Pass
Co (0.4 x 0.4)	0.41mA/um	>0.64	Pass	>0.64	Pass	>0.63	Pass

*Stress Conditions: 175°C

Hot Carrier (HEI)

Lot #	Gate	Fail Criteria= .1% CUM @ Vcc+10%> 0.2yr	Reading (year)	Results*
C92050	20/0.3um	Idsat Shift >10%	0.52	Pass
C92051	20/0.3um	Idsat Shift >10%	0.46	Pass
C92054	20/0.3um	Idsat Shift >10%	0.68	Pass

Test Condition: 10 pieces, Vds=4.5V for 12k minutes @ 25C.

Gate Oxide Integrity (GOI)

Pattern		C92050	C92051	C92054
(A)	Mode A Fail (%)	0	0	0
N-Well: 180,00um^2;	Mode B Fail (%)	0.34	0	0
Tox=70Å	Yield	99.66	100	100
(B)	Mode A Fail (%)	0	0	0
P-Well: 180,00um^2;	Mode B Fail (%)	0.34	0	0
Tox=70Å	Yield	99.66	100	100

Mode A: Vbd <=3.3V
Mode B: 3.3VVbd <8V